

## 4-Mbit (512K x 8) Static RAM

### Features

- Very high speed: 45 ns
- Voltage range: 4.5V–5.5V
- Pin compatible with CY62148B
- Ultra low standby power
  - Typical standby current: 1  $\mu$ A
  - Maximum standby current: 7  $\mu$ A (Industrial)
- Ultra low active power
  - Typical active current: 2.0 mA @ f = 1 MHz
- Easy memory expansion with  $\overline{CE}$ , and  $\overline{OE}$  features
- Automatic power down when deselected
- CMOS for optimum speed and power
- Available in Pb-free 32-pin TSOP II and 32-pin SOIC <sup>[2]</sup> packages

### Functional Description <sup>[1]</sup>

The CY62148E is a high performance CMOS static RAM organized as 512K words by 8 bits. This device features advanced circuit design to provide ultra low active current. This is ideal for providing More Battery Life™ (MoBL<sup>®</sup>) in portable applications such as cellular telephones. The device also has an automatic power down feature that significantly reduces power consumption when addresses are not toggling. Placing the device into standby mode reduces power consumption by more than 99% when deselected ( $\overline{CE}$  HIGH). The eight input and output pins (IO<sub>0</sub> through IO<sub>7</sub>) are placed in a high impedance state when:

- Deselected ( $\overline{CE}$  HIGH)
- Outputs are disabled ( $\overline{OE}$  HIGH)
- Write operation is active ( $\overline{CE}$  LOW and  $\overline{WE}$  LOW)

To write to the device, take Chip Enable ( $\overline{CE}$ ) and Write Enable ( $\overline{WE}$ ) inputs LOW. Data on the eight IO pins (IO<sub>0</sub> through IO<sub>7</sub>) is then written into the location specified on the address pins (A<sub>0</sub> through A<sub>18</sub>).

To read from the device, take Chip Enable ( $\overline{CE}$ ) and Output Enable ( $\overline{OE}$ ) LOW while forcing Write Enable ( $\overline{WE}$ ) HIGH. Under these conditions, the contents of the memory location specified by the address pins appear on the IO pins.

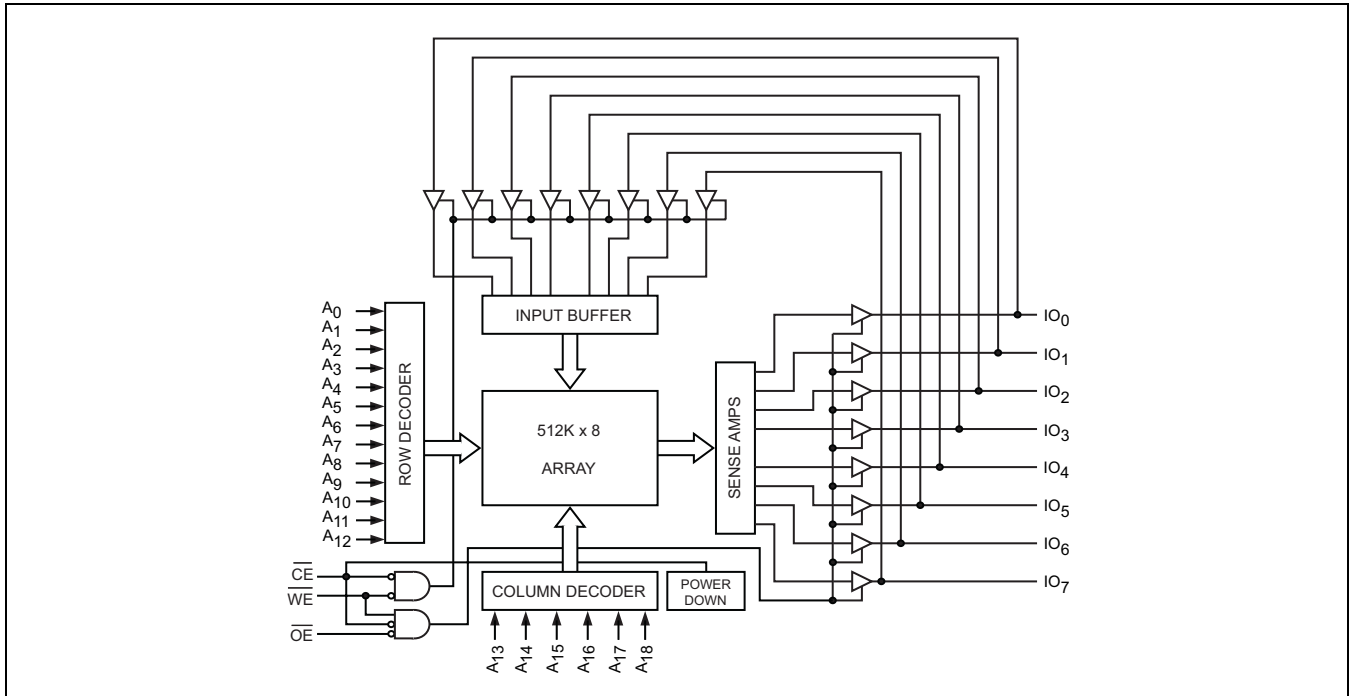
### Product Portfolio

Product		Range	V <sub>CC</sub> Range (V)			Speed (ns)	Power Dissipation					
							Operating I <sub>CC</sub> (mA)				Standby I <sub>SB2</sub> ( $\mu$ A)	
							f = 1MHz		f = f <sub>max</sub>			
Min	Typ <sup>[3]</sup>	Max	Typ <sup>[3]</sup>	Max	Typ <sup>[3]</sup>	Max	Typ <sup>[3]</sup>	Max				
CY62148ELL	TSOP II	Ind'l	4.5	5.0	5.5	45	2	2.5	15	20	1	7
CY62148ELL	SOIC	Ind'l/Auto-A	4.5	5.0	5.5	55	2	2.5	15	20	1	7

#### Notes

1. For best practice recommendations, refer to the Cypress application note "System Design Guidelines" at <http://www.cypress.com>.
2. SOIC package is available only in 55 ns speed bin.
3. Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at V<sub>CC</sub> = V<sub>CC(typ)</sub>, T<sub>A</sub> = 25°C.

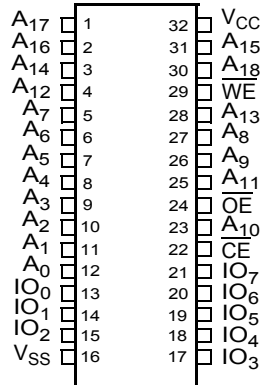
**Logic Block Diagram**



**Pin Configuration [2, 4]**

**32-pin SOIC/T SOP II Pinout**

**Top View**



**Note**

4. NC pins are not connected on the die.

### Maximum Ratings

Exceeding maximum ratings may impair the useful life of the device. These user guidelines are not tested.

Storage Temperature ..... -65°C to + 150°C

Ambient Temperature with Power Applied..... -55°C to + 125°C

Supply Voltage to Ground Potential..... -0.5V to 6.0V ( $V_{CCmax} + 0.5V$ )

DC Voltage Applied to Outputs in High-Z State<sup>[5, 6]</sup>..... -0.5V to 6.0V ( $V_{CCmax} + 0.5V$ )

DC Input Voltage<sup>[5, 6]</sup>..... -0.5V to 6.0V ( $V_{CCmax} + 0.5V$ )

Output Current into Outputs (LOW)..... 20 mA

Static Discharge Voltage..... > 2001V (per MIL-STD-883, Method 3015)

Latch-up Current .....>200mA

### Operating Range

Device	Range	Ambient Temperature	$V_{CC}$ <sup>[7]</sup>
CY62148E	Ind'I/Auto-A	-40°C to +85°C	4.5V to 5.5V

### Electrical Characteristics (Over the Operating Range)

Parameter	Description	Test Conditions	45 ns			55 ns <sup>[2]</sup>			Unit	
			Min	Typ <sup>[3]</sup>	Max	Min	Typ <sup>[3]</sup>	Max		
$V_{OH}$	Output HIGH Voltage	$I_{OH} = -1$ mA	2.4			2.4			V	
$V_{OL}$	Output LOW Voltage	$I_{OL} = 2.1$ mA			0.4			0.4	V	
$V_{IH}$	Input HIGH Voltage	$V_{CC} = 4.5V$ to 5.5V	2.2		$V_{CC} + 0.5$	2.2		$V_{CC} + 0.5$	V	
$V_{IL}$	Input LOW voltage	$V_{CC} = 4.5V$ to 5.5V	For TSOPII package		-0.5					V
			For SOIC package				-0.5		0.6 <sup>[8]</sup>	
$I_{IX}$	Input Leakage Current	$GND \leq V_I \leq V_{CC}$	-1		+1	-1		+1	$\mu A$	
$I_{OZ}$	Output Leakage Current	$GND \leq V_O \leq V_{CC}$ , Output Disabled	-1		+1	-1		+1	$\mu A$	
$I_{CC}$	$V_{CC}$ Operating Supply Current	$f = f_{max} = 1/t_{RC}$		15	20		15	20	mA	
		$f = 1$ MHz		2	2.5		2	2.5		
$I_{SB2}$ <sup>[9]</sup>	Automatic CE Power down Current — CMOS Inputs	$\overline{CE} \geq V_{CC} - 0.2V$ $V_{IN} \geq V_{CC} - 0.2V$ or $V_{IN} \leq 0.2V$ , $f = 0$ , $V_{CC} = V_{CC(max)}$		1	7		1	7	$\mu A$	

### Capacitance (For All Packages)<sup>[10]</sup>

Parameter	Description	Test Conditions	Max	Unit
$C_{IN}$	Input Capacitance	$T_A = 25^\circ C$ , $f = 1$ MHz,	10	pF
$C_{OUT}$	Output Capacitance	$V_{CC} = V_{CC(typ)}$	10	pF

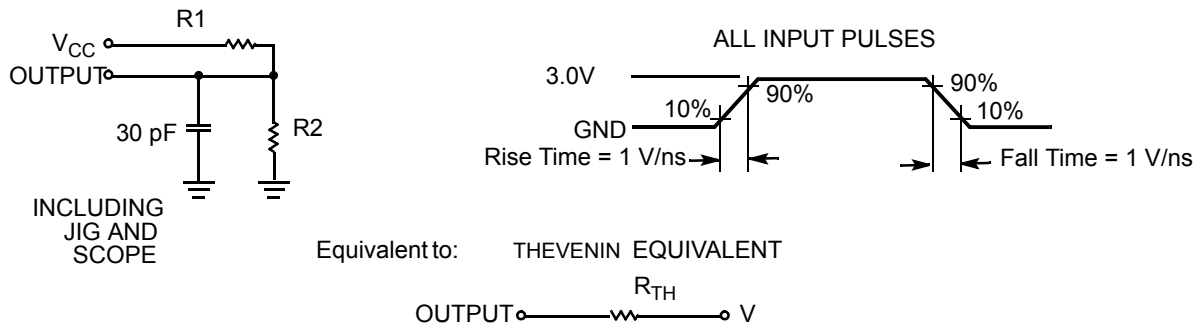
#### Notes

- $V_{L(min)}$  = -2.0V for pulse durations less than 20 ns for  $I \leq 30$  mA.
- $V_{IH(max)}$  =  $V_{CC} + 0.75V$  for pulse durations less than 20 ns.
- Full device AC operation assumes a minimum of 100  $\mu s$  ramp time from 0 to  $V_{CC(min)}$  and 200  $\mu s$  wait time after  $V_{CC}$  stabilization.
- Under DC conditions the device meets a  $V_{IL}$  of 0.8V. However, in dynamic conditions Input LOW Voltage applied to the device must not be higher than 0.6V. This is applicable to SOIC package only. Refer to AN13470 for details.
- Only chip enable ( $\overline{CE}$ ) must be HIGH at CMOS level to meet the  $I_{SB2}$  spec. Other inputs can be left floating.
- Tested initially and after any design or process changes that may affect these parameters.

**Thermal Resistance** <sup>[10]</sup>

Parameter	Description	Test Conditions	SOIC Package	TSOP II Package	Unit
$\Theta_{JA}$	Thermal Resistance (Junction to Ambient)	Still Air, soldered on a 3 × 4.5 inch, two-layer printed circuit board	75	77	°C/W
$\Theta_{JC}$	Thermal Resistance (Junction to Case)		10	13	°C/W

**AC Test Loads and Waveforms**

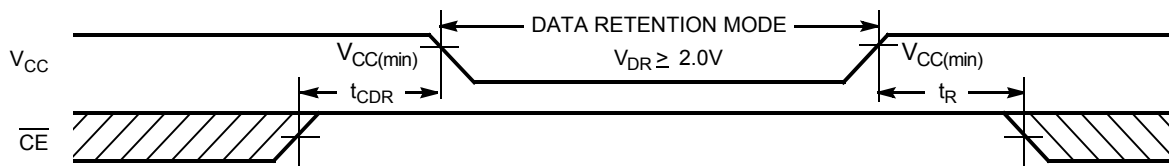


Parameters	5.0V	Unit
R1	1800	$\Omega$
R2	990	$\Omega$
$R_{TH}$	639	$\Omega$
$V_{TH}$	1.77	V

**Data Retention Characteristics** (Over the Operating Range)

Parameter	Description	Conditions	Min	Typ <sup>[3]</sup>	Max	Unit
$V_{DR}$	$V_{CC}$ for Data Retention		2			V
$I_{CCDR}$	Data Retention Current	$V_{CC} = V_{DR}$ , $\overline{CE} \geq V_{CC} - 0.2V$ , $V_{IN} \geq V_{CC} - 0.2V$ or $V_{IN} \leq 0.2V$		1	7	$\mu A$
$t_{CDR}^{[10]}$	Chip Deselect to Data Retention Time		0			ns
$t_R^{[11]}$	Operation Recovery Time		$t_{RC}$			ns

**Data Retention Waveform**



**Note**

11. Full device operation requires linear  $V_{CC}$  ramp from  $V_{DR}$  to  $V_{CC(min)} \geq 100 \mu s$  or stable at  $V_{CC(min)} \geq 100 \mu s$ .

**Switching Characteristics** (Over the Operating Range) <sup>[12]</sup>

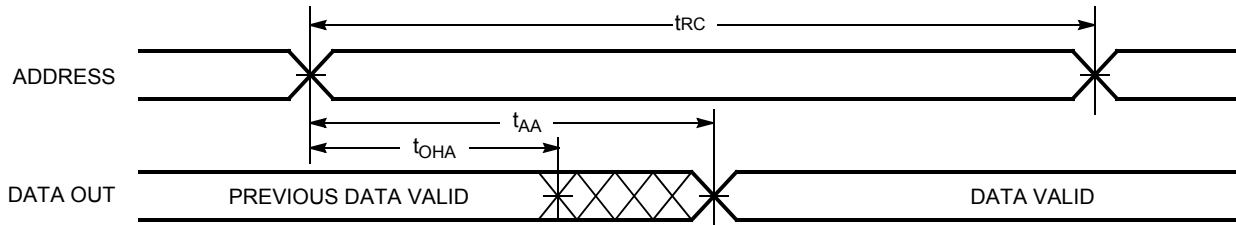
Parameter	Description	45 ns		55 ns <sup>[2]</sup>		Unit
		Min	Max	Min	Max	
<b>Read Cycle</b>						
$t_{RC}$	Read Cycle Time	45		55		ns
$t_{AA}$	Address to Data Valid		45		55	ns
$t_{OHA}$	Data Hold from Address Change	10		10		ns
$t_{ACE}$	$\overline{CE}$ LOW to Data Valid		45		55	ns
$t_{DOE}$	$\overline{OE}$ LOW to Data Valid		22		25	ns
$t_{LZOE}$	$\overline{OE}$ LOW to LOW Z <sup>[13]</sup>	5		5		ns
$t_{HZOE}$	$\overline{OE}$ HIGH to High Z <sup>[13, 14]</sup>		18		20	ns
$t_{LZCE}$	$\overline{CE}$ LOW to Low Z <sup>[13]</sup>	10		10		ns
$t_{HZCE}$	$\overline{CE}$ HIGH to High Z <sup>[13, 14]</sup>		18		20	ns
$t_{PU}$	$\overline{CE}$ LOW to Power up	0		0		ns
$t_{PD}$	$\overline{CE}$ HIGH to Power down		45		55	ns
<b>Write Cycle <sup>[15]</sup></b>						
$t_{WC}$	Write Cycle Time	45		55		ns
$t_{SCE}$	$\overline{CE}$ LOW to Write End	35		40		ns
$t_{AW}$	Address Setup to Write End	35		40		ns
$t_{HA}$	Address Hold from Write End	0		0		ns
$t_{SA}$	Address Setup to Write Start	0		0		ns
$t_{PWE}$	$\overline{WE}$ Pulse Width	35		40		ns
$t_{SD}$	Data Setup to Write End	25		25		ns
$t_{HD}$	Data Hold from Write End	0		0		ns
$t_{HZWE}$	$\overline{WE}$ LOW to High-Z <sup>[13, 14]</sup>		18		20	ns
$t_{LZWE}$	$\overline{WE}$ HIGH to Low-Z <sup>[13]</sup>	10		10		ns

**Notes**

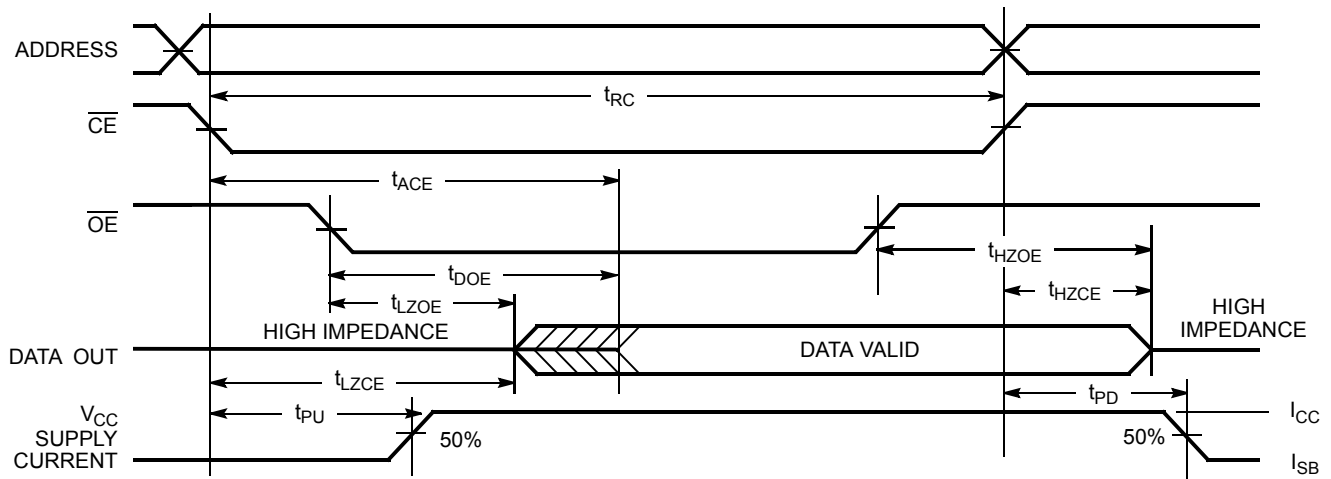
12. Test conditions for all parameters other than tri-state parameters assume signal transition time of 3 ns or less, timing reference levels of 1.5V, input pulse levels of 0 to 3V, and output loading of the specified  $I_{OL}/I_{OH}$  as shown in the "AC Test Loads and Waveforms" on page 4.
13. At any given temperature and voltage condition,  $t_{HZCE}$  is less than  $t_{LZCE}$ ,  $t_{HZOE}$  is less than  $t_{LZOE}$ , and  $t_{HZWE}$  is less than  $t_{LZWE}$  for any given device.
14.  $t_{HZOE}$ ,  $t_{HZCE}$ , and  $t_{HZWE}$  transitions are measured when the outputs enter a high impedance state.
15. The internal write time of the memory is defined by the overlap of  $\overline{WE}$ ,  $\overline{CE} = V_{IL}$ . All signals must be ACTIVE to initiate a write and any of these signals can terminate a write by going INACTIVE. The data input setup and hold timing should be referenced to the edge of the signal that terminates the write.

## Switching Waveforms

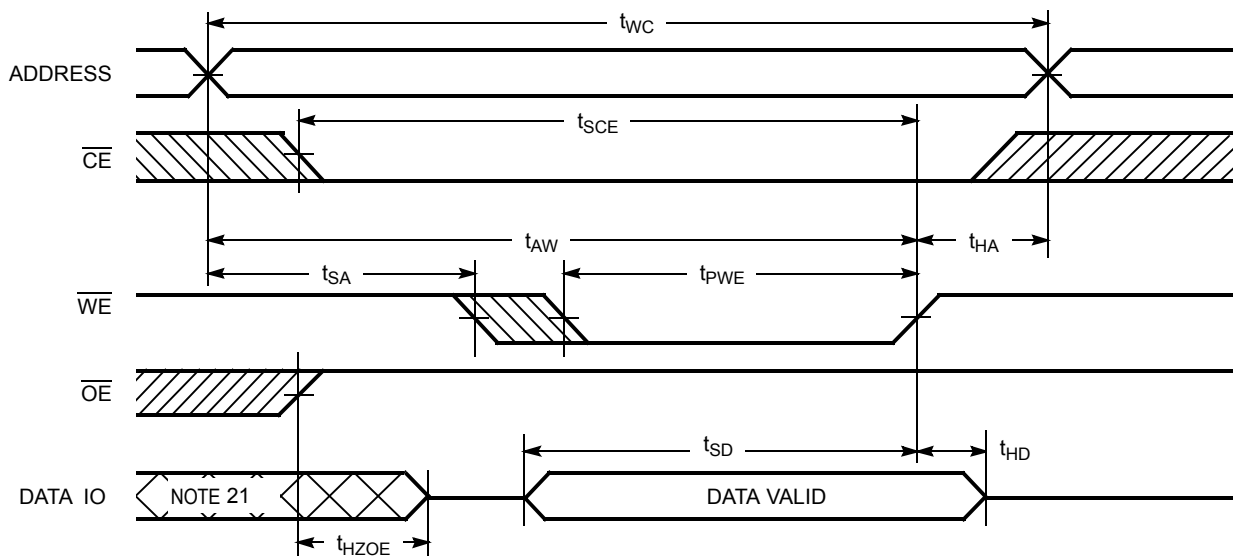
**Read Cycle No. 1 (Address Transition Controlled)** [16, 17]



**Read Cycle No. 2 ( $\overline{OE}$  Controlled)** [17, 18]



**Write Cycle No. 1 ( $\overline{WE}$  Controlled,  $\overline{OE}$  HIGH During Write)** [19, 20]

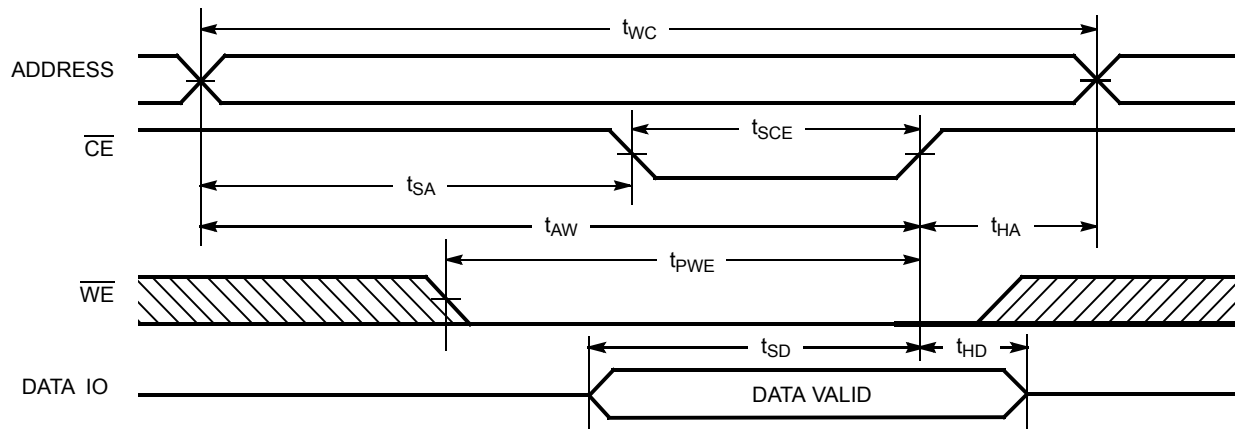


**Notes:**

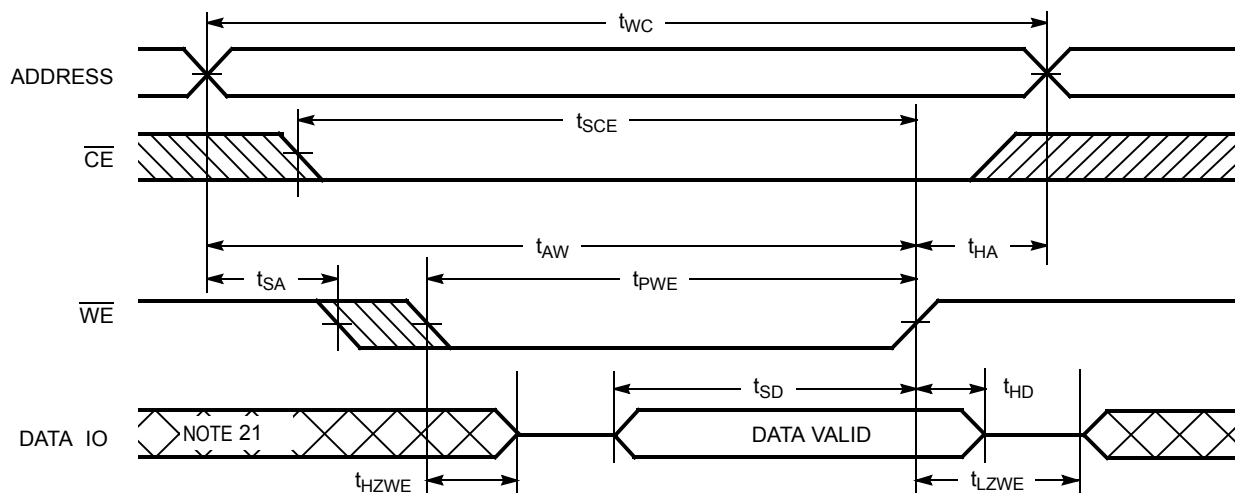
- 16. Device is continuously selected.  $\overline{OE}$ ,  $\overline{CE} = V_{IL}$ .
- 17.  $\overline{WE}$  is HIGH for read cycles.
- 18. Address valid before or similar to  $\overline{CE}$  transition LOW.
- 19. Data IO is high impedance if  $\overline{OE} = V_{IH}$ .
- 20. If  $\overline{CE}$  goes HIGH simultaneously with  $\overline{WE}$  HIGH, the output remains in high impedance state.
- 21. During this period, the IOs are in output state and input signals must not be applied.

**Switching Waveforms** (continued)

**Write Cycle No. 2** ( $\overline{CE}$  Controlled) [19, 20]



**Write Cycle No. 3** ( $\overline{WE}$  Controlled,  $\overline{OE}$  LOW) [20]



**Truth Table**

$\overline{CE}$	$\overline{WE}$	$\overline{OE}$	IO's	Mode	Power
H	X	X	High Z	Deselect/Power down	Standby ( $I_{SB}$ )
L	H	L	Data Out	Read	Active ( $I_{CC}$ )
L	L	X	Data In	Write	Active ( $I_{CC}$ )
L	H	H	High Z	Selected, Outputs Disabled	Active ( $I_{CC}$ )

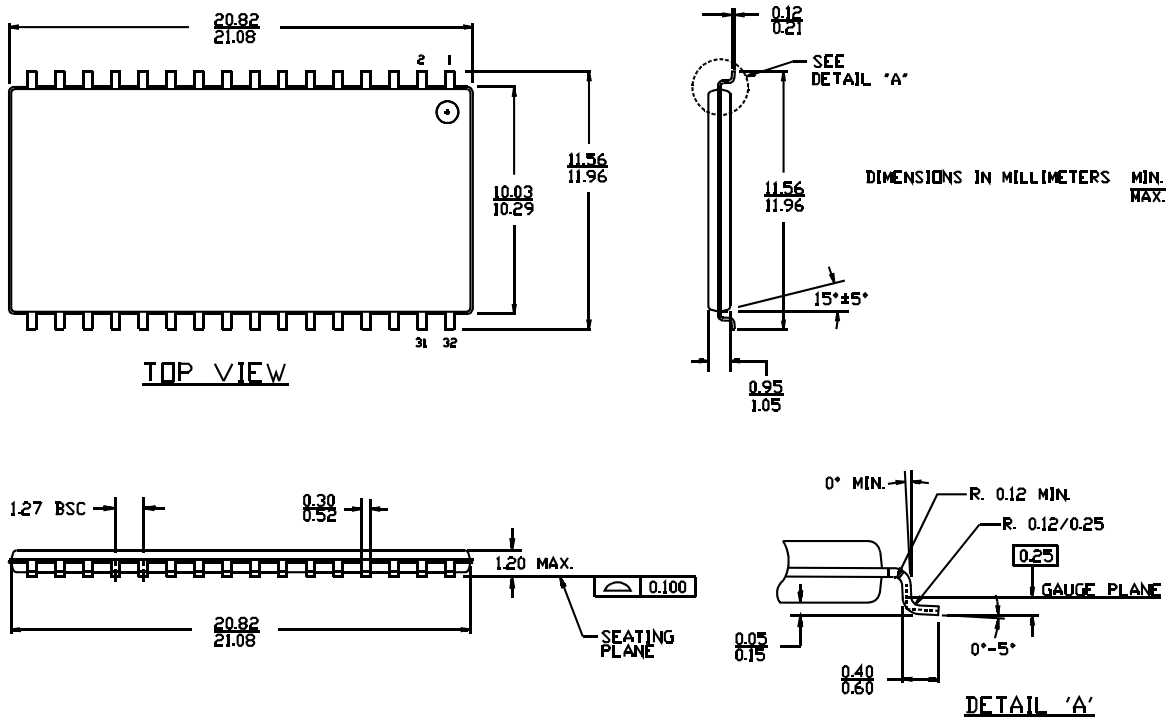
Ordering Information

Speed (ns)	Ordering Code	Package Diagram	Package Type	Operating Range
45	CY62148ELL-45ZSXI	51-85095	32-pin Thin Small Outline Package II (Pb-free)	Industrial
55	CY62148ELL-55SXI	51-85081	32-pin Small Outline Integrated Circuit (Pb-free)	Industrial
55	CY62148ELL-55SXA	51-85081	32-pin Small Outline Integrated Circuit (Pb-free)	Automotive-A

Contact your local Cypress sales representative for availability of these parts.

Package Diagrams

Figure 1. 32-pin TSOP II, 51-85095

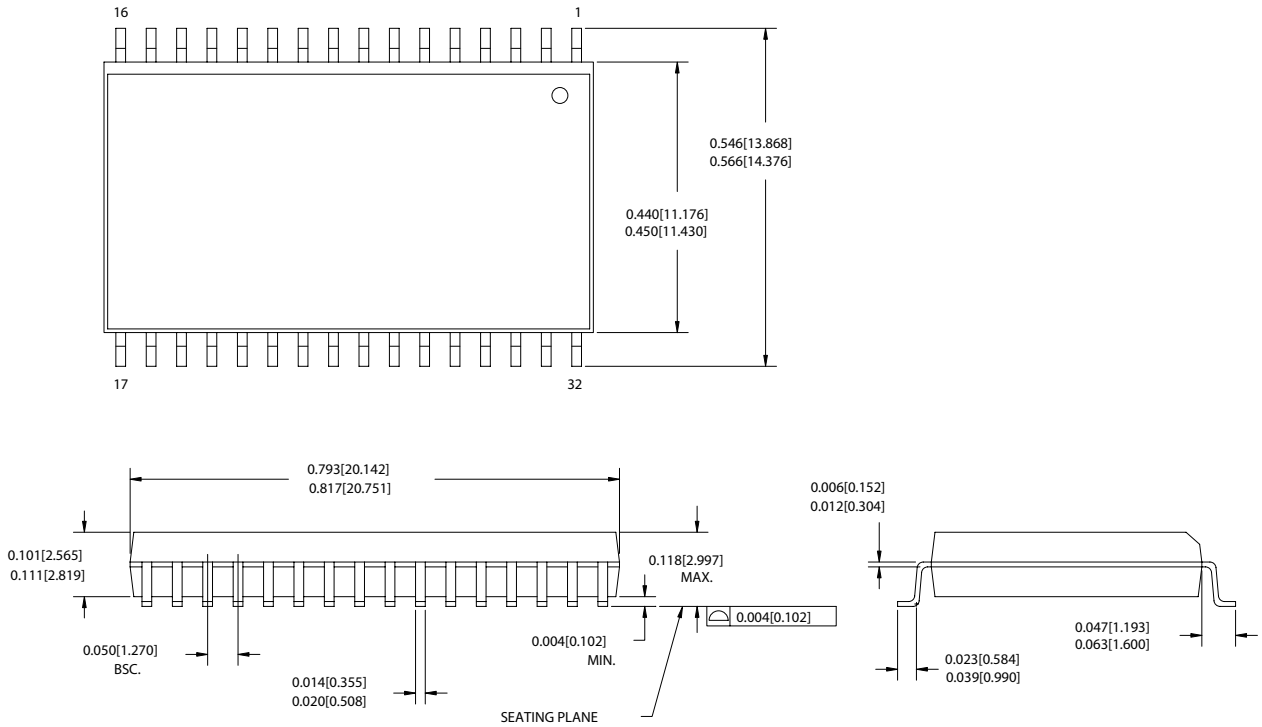


51-85095-\*\*



Package Diagrams (continued)

Figure 2. 32-pin (450 MIL) Molded SOIC, 51-85081



51-85081-\*B

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**Document History Page**

Document Title: CY62148E MoBL <sup>®</sup> , 4-Mbit (512K x 8) Static RAM Document Number: 38-05442				
REV.	ECN NO.	Issue Date	Orig. of Change	Description of Change
**	201580	01/08/04	AJU	New Data Sheet
*A	249276	See ECN	SYT	<p>Changed from Advance Information to Preliminary</p> <p>Moved Product Portfolio to Page 2</p> <p>Added RTSOP II and Removed FBGA Package</p> <p>Changed V<sub>CC</sub> stabilization time in footnote #7 from 100 μs to 200 μs</p> <p>Changed I<sub>CCDR</sub> from 2.0 μA to 2.5 μA</p> <p>Changed typo in Data Retention Characteristics(t<sub>R</sub>) from 100 μs to t<sub>RC</sub> ns</p> <p>Changed t<sub>OHA</sub> from 6 ns to 10 ns for both 35 ns and 45 ns Speed Bin</p> <p>Changed t<sub>HZOE</sub>, t<sub>HZWE</sub> from 12 to 15 ns for 35 ns Speed Bin and 15 to 18 ns for 45 ns Speed Bin</p> <p>Changed t<sub>SCE</sub> from 25 to 30 ns for 35 ns Speed Bin and 40 to 35 ns for 45 ns Speed Bin</p> <p>Changed t<sub>HZCE</sub> from 12 to 18 ns for 35 ns Speed Bin and 15 to 22 ns for 45 ns Speed Bin</p> <p>Changed t<sub>SD</sub> from 15 to 18 ns for 35 ns Speed Bin and 20 to 22 ns for 45 ns Speed Bin</p> <p>Changed t<sub>DOE</sub> from 15 to 18 ns for 35 ns Speed Bin</p> <p>Corrected typo in Package Name</p> <p>Changed Ordering Information to include Pb-Free Packages</p>
*B	414820	See ECN	ZSD	<p>Changed from Preliminary to Final</p> <p>Changed the address of Cypress Semiconductor Corporation on Page #1 from "3901 North First Street" to "198 Champion Court"</p> <p>Removed 35ns Speed Bin</p> <p>Removed "L" version of CY62148E</p> <p>Changed I<sub>CC</sub> (Typ) value from 1.5 mA to 2 mA at f=1 MHz</p> <p>Changed I<sub>CC</sub> (Max) value from 2 mA to 2.5 mA at f=1 MHz</p> <p>Changed I<sub>CC</sub> (Typ) value from 12 mA to 15 mA at f=f<sub>max</sub></p> <p>Removed I<sub>SB1</sub> spec from the Electrical characteristics table</p> <p>Changed I<sub>SB2</sub> Typ values from 0.7 μA to 1 μA and Max values from 2.5 μA to 7 μA</p> <p>Modified footnote #4 to include current limit</p> <p>Removed redundant footnote on DNU pins</p> <p>Changed the AC testload capacitance from 100 pF to 30 pF on page #4</p> <p>Changed test load parameters R1, R2, R<sub>TH</sub> and V<sub>TH</sub> from 1838 Ω, 994 Ω, 645 Ω and 1.75V to 1800 Ω, 990 Ω, 639 Ω and 1.77V</p> <p>Changed I<sub>CCDR</sub> from 2.5 μA to 7 μA</p> <p>Added I<sub>CCDR</sub> typical value</p> <p>Changed t<sub>LZOE</sub> from 3 ns to 5 ns</p> <p>Changed t<sub>LZCE</sub> and t<sub>LZWE</sub> from 6 ns to 10 ns</p> <p>Changed t<sub>HZCE</sub> from 22 ns to 18 ns</p> <p>Changed t<sub>PWE</sub> from 30 ns to 35 ns</p> <p>Changed t<sub>SD</sub> from 22 ns to 25 ns</p> <p>Updated the ordering information table and replaced Package Name column with Package Diagram</p>
*C	464503	See ECN	NXR	<p>Included Automotive Range in product offering</p> <p>Updated the Ordering Information</p>
*D	485639	See ECN	VKN	Corrected the operating range to 4.5V - 5.5V on page# 3
*E	833080	See ECN	VKN	<p>Added footnote #8</p> <p>Added V<sub>IL</sub> spec for SOIC package</p>
*F	890962	See ECN	VKN	<p>Added Automotive-A part and its related information</p> <p>Removed Automotive-E part and its related information</p> <p>Added footnote #2 related to SOIC package</p> <p>Added footnote #9 related to I<sub>SB2</sub></p> <p>Added AC values for 55 ns Industrial-SOIC range</p> <p>Updated Ordering Information table</p>